

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:) Group Art Unit:
Eric J. Bergman) Examiner:
Serial No.: Not yet assigned)
Filed:)
For: METHODS FOR CLEANING)
SEMICONDUCTOR SURFACES)

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

IN THE CLAIMS

Please cancel original claims 1-90 and add new claims 91-97 as shown on the attached claim sheets.

REMARKS

This application is a continuation of Serial No. 08/853,649 (which will soon issue) examined by Examiner Goudreau in Art Unit 1765.

Dated: March 19, 2001

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(37 C.F.R. §1.10)

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Claim Sheet – Preliminary Amendment

Docket 261/136

91. A method for cleaning a semiconductor article, comprising the steps of:

contacting the article with an oxidizing solution;

rinsing the article; and

exposing the article to a vapor comprising ozone.

92. A method for cleaning a surface of a semiconductor article, comprising the steps of:

loading the semiconductor article into a chamber;

providing a heated liquid solution onto the surface of the article within the chamber, the solution including deionized water;

providing ozone into the chamber; and

rotating the article within the chamber with the heated liquid solution on the surface of the article.

93. The method of claim 92 where the solution is heated to a temperature between room temperature and 100°C.

94. The method of claim 92 where the solution is heated to a temperature between 50-90°C.

95. The method of claim 92 where the article is rotated at 200-2000rpm.

96. The method of claim 91 with the liquid further including hydrogen fluoride.

97. A method for cleaning a semiconductor article, comprising the steps of:
- contacting the article with a heated oxidizing solution;
 - exposing the article to a vapor comprising ozone;
 - rotating the article; and
 - rinsing the article.